



# BTA420Y-800BT

3Q Hi-Com Triac

23 June 2014

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78D (TO-220AB) internally insulated plastic package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series BT" triac will commute the full RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150\text{ }^{\circ}\text{C}$ ) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- 2500 V RMS isolation voltage capability
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- High junction operating temperature capability
- High voltage capability
- Least sensitive gate for highest noise immunity
- Internally insulated package
- Internally isolated mounting base
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

## 3. Applications

- Applications subject to high temperature
- Heating controls
- High power motor control
- High power switching

## 4. Quick reference data

Table 1. Quick reference data

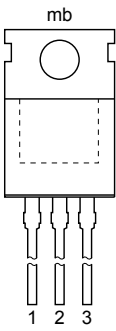
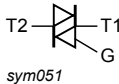
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	200	A
$T_j$	junction temperature		-	-	150	$^{\circ}\text{C}$



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 100\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	20	A
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	1800	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ; $I_{T(RMS)} = 20\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	25	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220AB (SOT78D)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BTA420Y-800BT	TO-220AB	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220	SOT78D

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BTA420Y-800BT	BTA420Y-800BT

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 100\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	20	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	200	A
		full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$	-	220	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	200	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_T = 24\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}\text{C}$
$T_j$	junction temperature		-	150	$^{\circ}\text{C}$

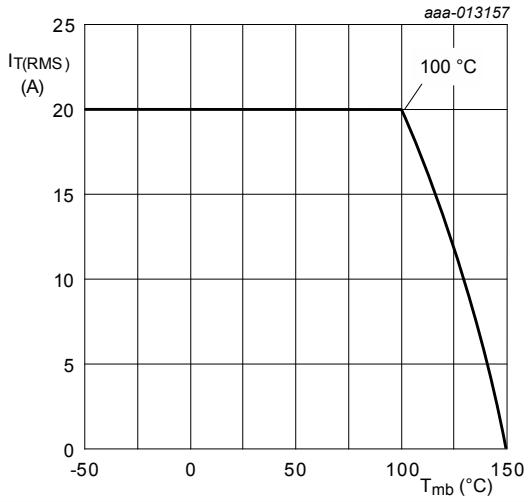


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

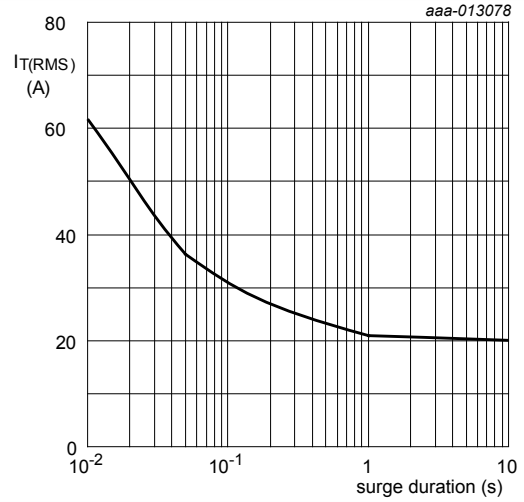
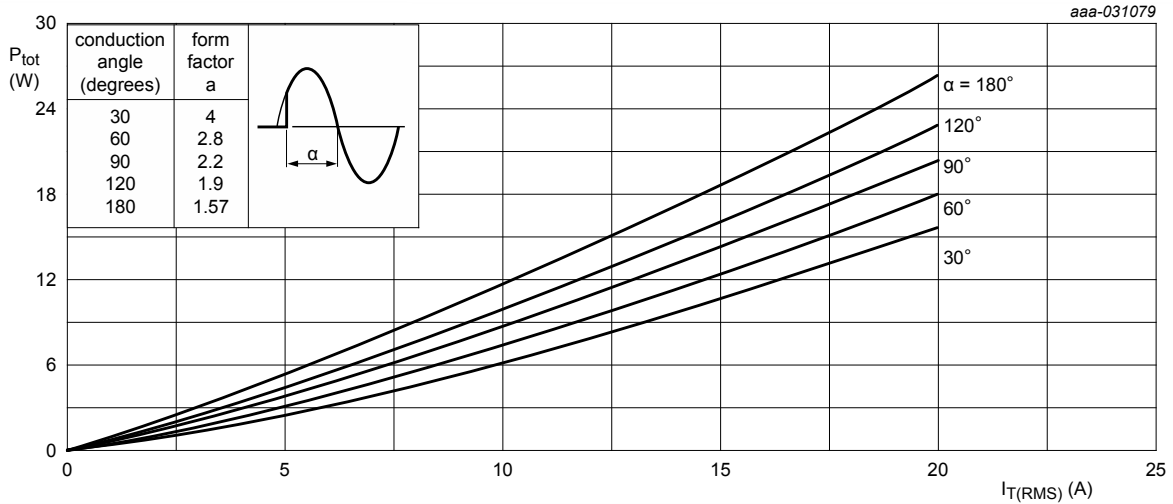
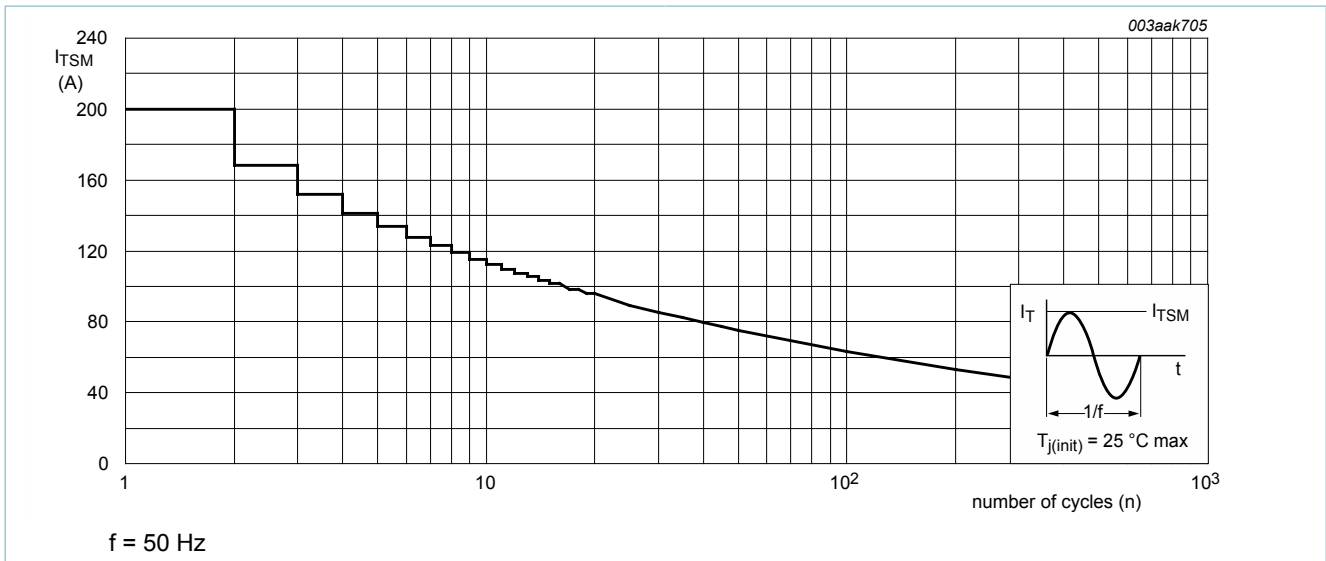


Fig. 2. RMS on-state current as a function of surge duration; maximum values  
f = 50 Hz; T<sub>mb</sub> = 100 °C

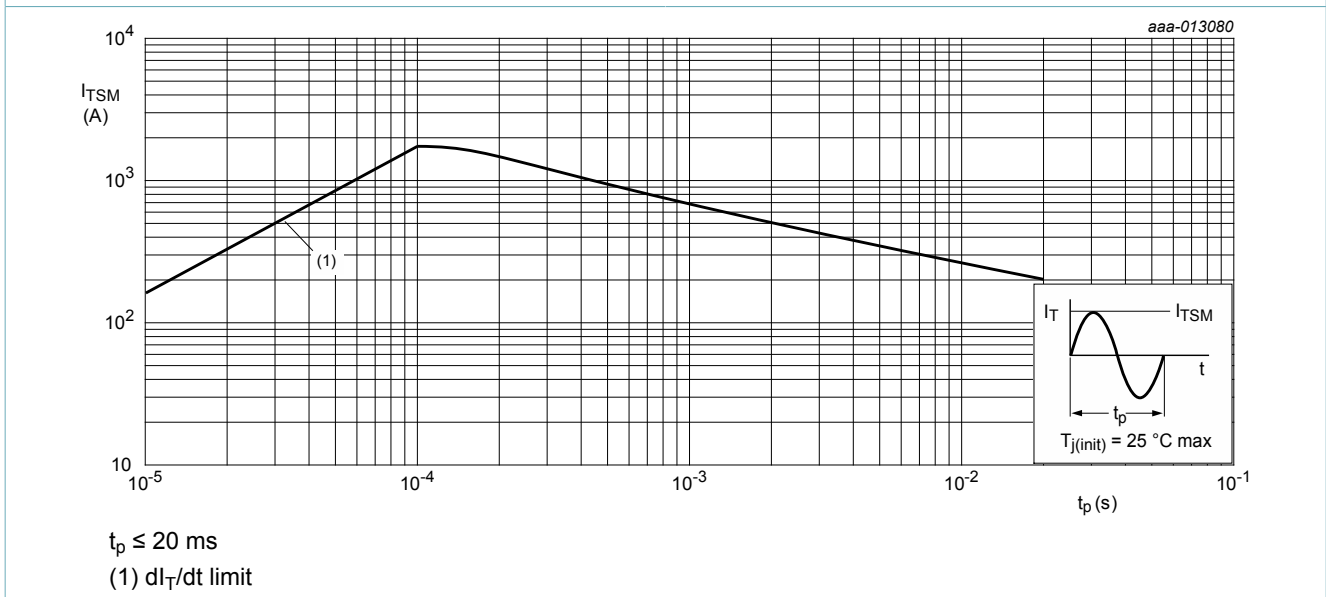


$\alpha$  = conduction angle  
 $a$  = form factor =  $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



**Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values**

## 9. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; <a href="#">Fig. 6</a>	-	-	1.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

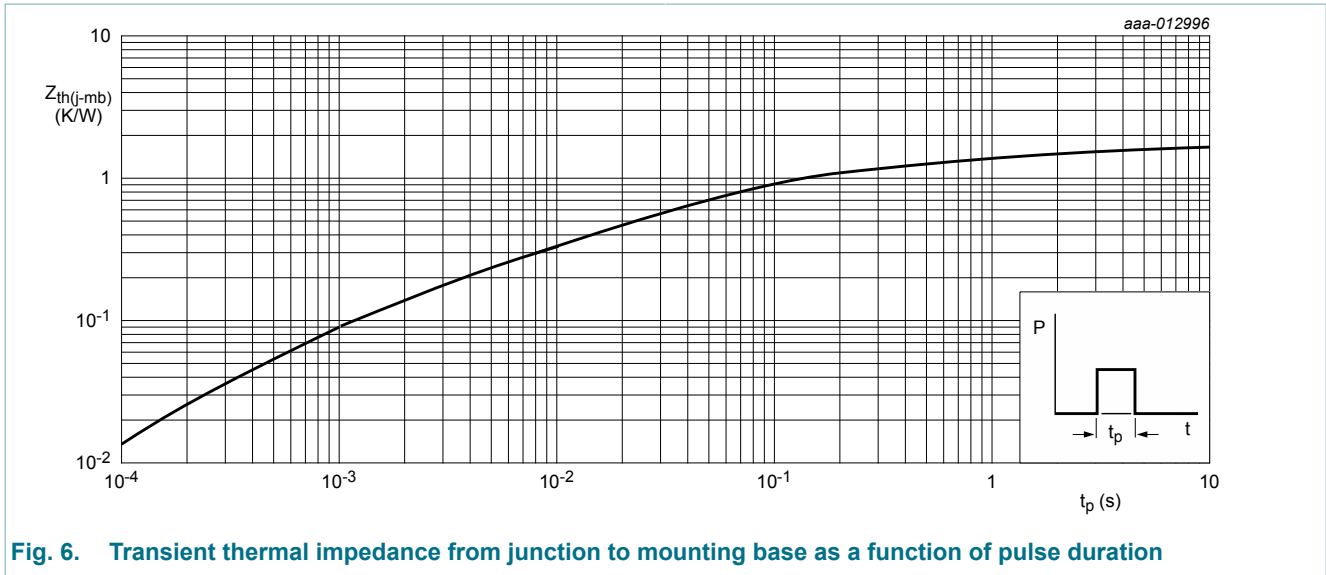


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Isolation characteristics

Table 7. Isolation characteristics

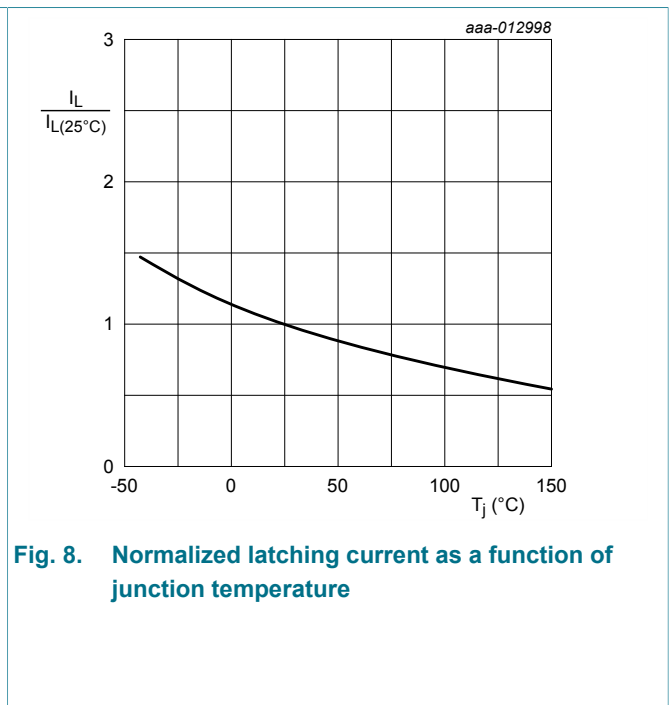
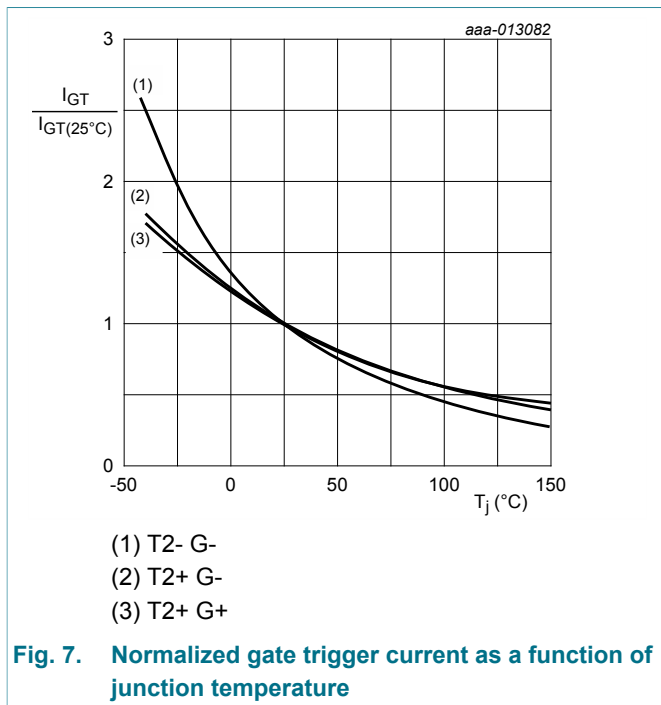
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_{mb} = 25\text{ }^\circ\text{C}$	-	-	2500	V
$C_{isol}$	isolation capacitance	from main terminal 2 to external heatsink; $f = 1\text{ MHz}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$	-	10	-	pF

## 11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	60	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	90	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2\text{- G-}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	-	60	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 9</a>	-	-	60	mA
$V_T$	on-state voltage	$I_T = 24\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 10</a>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	-	0.7	1	V
		$V_D = 400\text{ V}; T_j = 150\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	0.2	0.4	-	V
$I_D$	off-state current	$V_D = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	0.2	1	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}; T_j = 150\text{ }^\circ\text{C}; (V_{DM} = 67\% \text{ of } V_{DRM});$ exponential waveform; gate open circuit	1800	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}; T_j = 150\text{ }^\circ\text{C}; I_{T(RMS)} = 20\text{ A}; dV_{com}/dt = 10\text{ V}/\mu\text{s};$ gate open circuit	25	-	-	A/ms
		$V_D = 400\text{ V}; T_j = 150\text{ }^\circ\text{C}; I_{T(RMS)} = 20\text{ A}; dV_{com}/dt = 1\text{ V}/\mu\text{s};$ gate open circuit	65	-	-	A/ms



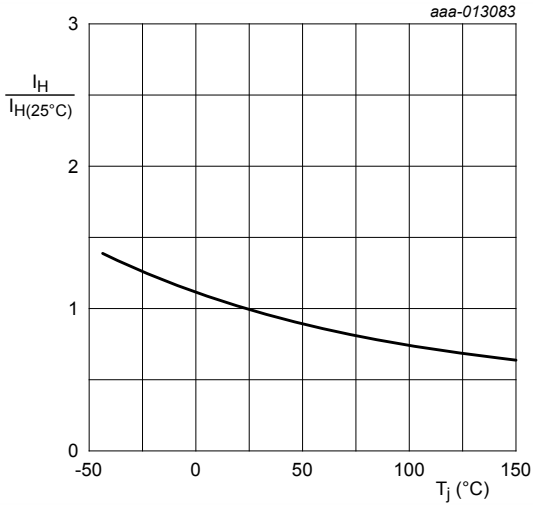
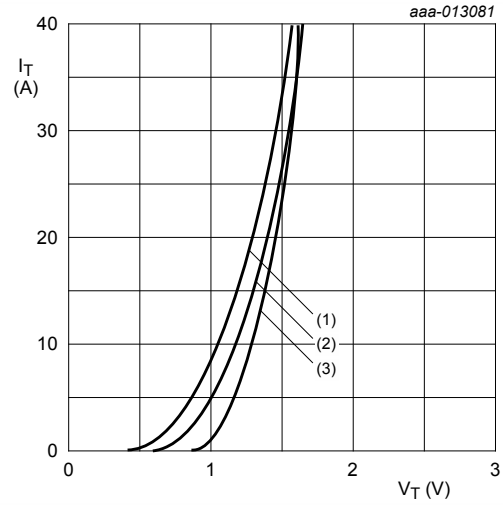


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 0.998 \text{ V}$ ;  $R_s = 0.020 \Omega$

- (1)  $T_j = 150 \text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 150 \text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

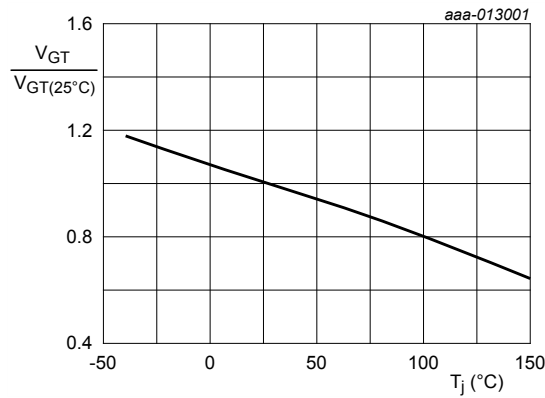


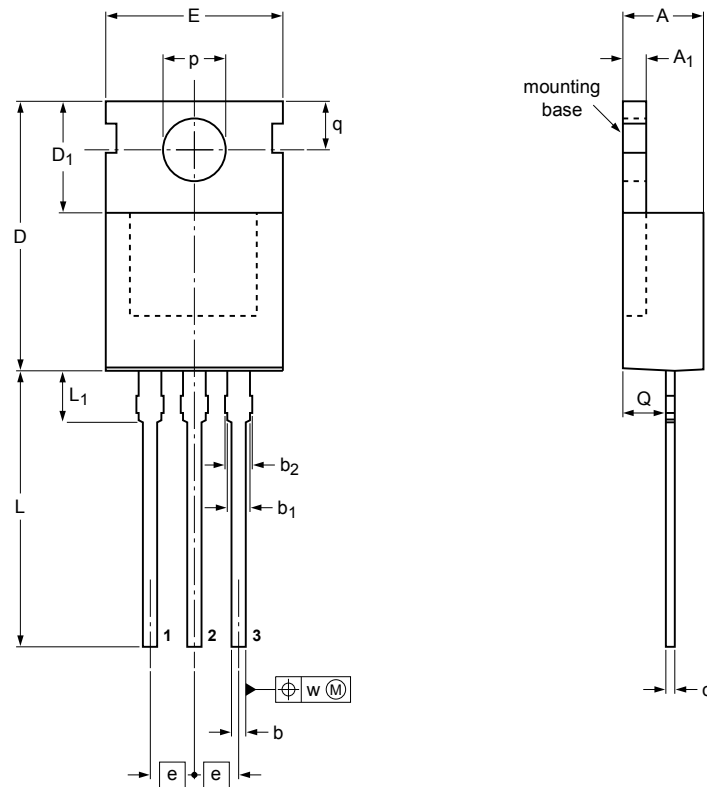
Fig. 11. Normalized gate trigger voltage as a function of junction temperature



## 12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220

SOT78D



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub> ref	E	e	L	L <sub>1</sub> ref	p	Q	q	w
mm	4.7 4.3	1.40 1.25	0.9 0.6	1.4 1.1	1.72 1.32	0.6 0.4	16.0 15.2	6.5	10.3 9.7	2.54	14.0 12.8	3.0	3.7 3.5	2.6 2.2	3.0 2.7	0.2

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78D		TO-220			07-04-04 07-07-10

Fig. 12. Package outline TO-220AB (SOT78D)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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